

AMENDMENTS TO THE SPECIFICATION

Please amend the sentence in the "CROSS REFERENCE TO A RELATED APPLICATION" section as follows:

This application is a division of application Ser. No. 10/207,352, filed July 29, 2002, now United States Patent 6,740,535.

Please amend the section titled "BRIEF DESCRIPTION OF THE DRAWINGS" from line 10 on page 7 until line 7 on page 8 as follows:

These and other features of the present invention will become apparent from the accompanying detailed description and drawings.

Fig. 1 shows prior art in a cross-sectional view of a free (freestanding) T-gate formed by conventional processing.

~~Fig. 2 shows~~ Figs. 2A - 2C show schematically the steps for forming a prior art side wall supported T-gate structure.

~~Fig. 3 shows~~ Figs. 3A - 3F show shows schematically the steps for forming enhanced T-gate structures.

~~Fig. 4 shows~~ Figs. 4A - 4C show schematically the steps of a further embodiment of the method for forming an enhanced T-gate structure.

~~Fig. 5 shows~~ Figs. 5A - 5B show shows schematically the self-aligned source/drain metallurgy steps for a prior art T-gate device, and for the enhanced T-gate device.

~~Fig. 6 shows~~ Figs. 6A - 6B show schematically a MODFET devices comprising an enhanced T-gate structure.

Fig. 7 shows symbolically an integrated circuit comprising a MODFET device

which in turn is comprising an enhanced T-gate structure.

~~Fig. 8 shows~~ Figs. 8A - 8B show shows the enhanced T-gate structures with voids under the T-bar portion after deposition of a first layer of interconnect dielectric.